

### IN THE CLAIMS

1-32. (Canceled)

33. (Currently Amended) A method for cleaning a support adapted to releasably hold a wafer, comprising:  
    providing a cleaning surface of a cleaning head assembly;  
    moving the cleaning surface into contact with the support adapted to releasably hold a wafer; and  
    removing contaminants from the support by vacuuming the contaminants through the cleaning head assembly.

34. (Original) The method of 33, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface into vertical alignment with the support.

35. (Original) The method of claim 33, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface into coaxial alignment with the support.

36. (Original) The method of claim 33, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface downwardly onto the support.

37. (Original) The method of claim 33, wherein the support has wafer supporting upper surface.

38. (Currently Amended) The method of claim 37, wherein the wafer supporting upper surface is a metal surface.

39. (Currently Amended) The method of claim 37, wherein the wafer supporting upper surface is a steel surface.

40. (Currently Amended) The method of claim 37, wherein the cleaning surface is a plastic.

41. (Currently Amended) The method of claim 37, wherein the cleaning surface includes polytetrafluoroethylene.

42. (Currently Amended) The method of claim 37, wherein the cleaning surface is homopolymer acetal.

43-54. (Canceled)

55. (Currently Amended) A method for cleaning a support adapted to releasably hold a wafer, comprising:

providing a cleaning surface;  
removing a wafer from the support adapted to releasably hold a wafer;  
thereafter, moving the cleaning surface into contact with the support; and  
removing contaminants from the support adapted to releasably hold a wafer by vacuuming the contaminants through the cleaning surface.

56. (Original) The method of 55, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface into vertical alignment with the support.

57. (Original) The method of 56, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface downwardly onto the support.

58. (Original) The method of claim 55, wherein removing contaminants from the support includes rotating the cleaning surface on the support.

59. (Original) The method of claim 55, wherein removing contaminants from the support includes rotating the support on the cleaning surface.

60. (Original) The method of claim 55, wherein removing contaminants from the support includes activating a vacuum source.

61. (Original) The method of claim 60, wherein activating a vacuum source includes activating a vacuum source when the cleaning surface contacts the support.

62. (Original) The method of claim 60, wherein activating a vacuum source includes activating a vacuum source when the support contacts the cleaning surface.

63-68. (Canceled)

69. (Currently Amended) Machine executable code stored on machine readable media, wherein the code comprises:  
    providing a cleaning surface;  
    moving the cleaning surface into contact with ~~the~~ a wafer support; and  
    removing contaminants from the wafer support by vacuuming the contaminants through the cleaning head assembly.

70. (Original) The code of 69, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface into vertical alignment with the support.

71. (Original) The code of 70, wherein moving the cleaning surface into contact with the support includes moving the cleaning surface downwardly onto the support.

72. (Original) The code of claim 69, wherein removing contaminants from the support includes rotating the cleaning surface on the support.

73. (Original) The code of claim 69, wherein removing contaminants from the support includes rotating the support on the cleaning surface.

74. (Original) The code of claim 69, wherein removing contaminants from the support includes activating a vacuum source.
75. (Original) The code of claim 69, wherein the activating a vacuum source includes activating a vacuum source when the support contacts the cleaning surface.
76. (Original) The code of claim 69, wherein the activating a vacuum source includes activating a vacuum source when the cleaning surface contacts the support.
77. (Original) The code of claim 69, wherein the activating a vacuum source includes generating a vacuum when the cleaning surface is a set distance from the head.
78. (Original) The code of claim 77, wherein the set distance is about 0.2 microns.
79. (Original) The code of claim 77, wherein the set distance is less than about 0.2 microns.
80. (Original) The code of claim 69, wherein the activating a vacuum source includes generating a vacuum when the cleaning surface is vertically aligned with the support.
81. (Original) The code of claim 69, wherein moving the cleaning surface into contact with the support is delayed until after removing a wafer from the support.
82. (Original) The code of claim 74, wherein the delay is at least 5 seconds.
- 83-100. (Canceled)